



SUMITOMO ELECTRIC

Advance

02.07.30

◆ **Features**

- Up to 2.5 Gb/s high speed operation
- Clocked (MS-D/FF) or Non-clocked operation can be selected
- Disable function of modulation current and bias current
- Bias current monitoring
- 3.3 V or - 3.3 V single Voltage Supply operation
- Up to 50 mA modulation current
- Up to 50 mA bias current
- Differential ECL compatible interface
- On-chip 50 Ω terminations
- Internal voltage reference for AC coupling

F0532506Q

3.3 V 2.5 Gb/s NRZ Data Rate

Laser Diode Driver



◆ **Applications**

- Laser diode driver of an optical transmitter circuit up to 2.5 Gb/s

◆ **Functional Description**

The F0532506Q is a high performance GaAs laser diode driver IC applicable in an optical transmitter circuit up to 2.5 Gb/s NRZ data rate (especially suitable for SDH [STM-16] / SONET [OC-48]).

The F0532506Q specifies the rise time and the fall time of 80 ps (20 % - 80 %, 25 Ω load) typically. It features the single +3.3 V or - 3.3 V supply operation, the modulation current between 4 mA and 50 mA, and the bias current between 4 mA and 50 mA.

◆ Absolute Maximum Ratings

T_a=25°C, unless specified.

Parameter	Symbol	Value	Units
Supply Voltage	V _{DD} - V _{SS}	- 0.3 to +4.0V	V
Supply Current *1	I _{CC}	200	mA
Input Voltage (D _{IN} , D _{INB} , CK _{IN} , CK _{INB})	V _{IN}	V _{DD} - 2.5 to V _{DD}	V
Input Voltage (DIS _{IN} , SEL _{IN})	V _{INC1}	V _{SS} to V _{DD} + 0.5	V
Input Voltage (V _{M1} , V _{B1})	V _{INC2}	V _{SS} to V _{SS} + 1.7	V
Input Voltage (V _{M0} , V _{B0})	V _{INC3}	V _{SS} to V _{SS} + 0.7	V
Input Voltage (V _{REG})	V _{INC4}	V _{SS} to V _{DD}	V
Output Voltage (OUT, OUT _B , OUT _{BIAS})	V _{OUT}	V _{DD} - 2.0 to V _{DD} + 0.5	V
Output Current (OUT, OUT _B , OUT _{BIAS})	I _{OUT}	0 to 70	mA
Output Voltage (BM, BM _B)	V _{OUTM}	V _{SS} to V _{DD} + 0.5	V
Termination Voltage (V _{TTD} , V _{TTCK})	V _{TT}	V _{DD} - 2.5 to V _{DD} + 0.5	V
Storage Temperature	T _{stg}	- 55 to + 125	°C
Ambient Operating Temperature	T _a	0 to + 70	°C

*1 Excluding the input current, the modulation current and the bias current.

◆ Recommended Operating Conditions

Parameter	Symbol	Value			Units
		Min.	Typ.	Max.	
Supply Voltage	V _{DD} - V _{SS}	3.10	3.30	3.50	V
Ambient Operating Temperature	T _a	0	25	70	°C

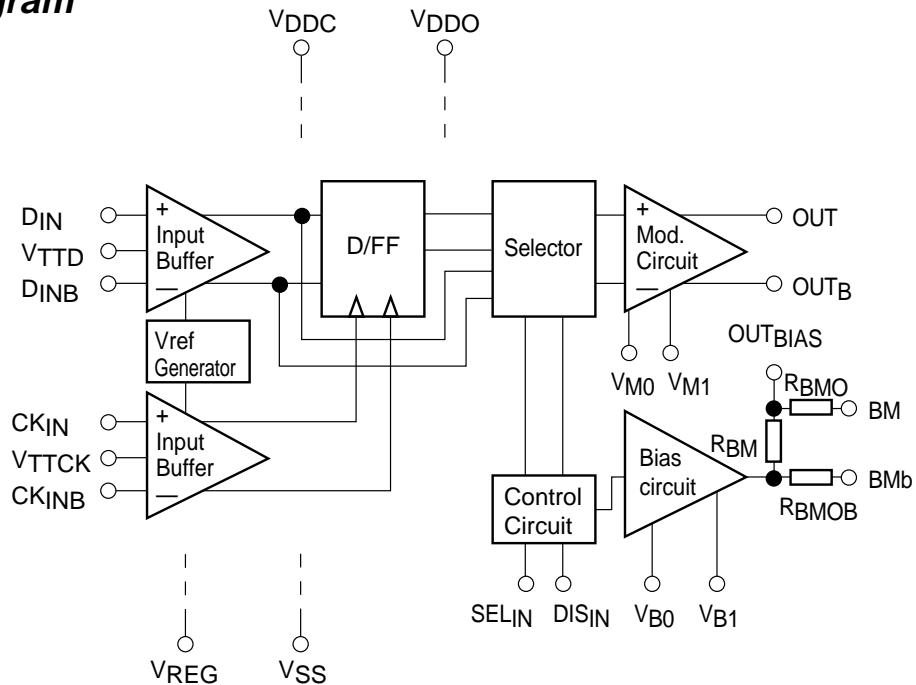
◆ Electrical Characteristics

T_a=25°C, V_{DD}-V_{SS} = 3.1 V to 3.5 V, V_{SS}=0 V, unless specified

Parameters	Symbol	Test Conditions	Value			Units
			Min.	Typ.	Max.	
Circuit Current *1	I _{CKT}	DC	-	80	115	mA
Input Voltage (ECL Interface)	V _{IH}	Differential Input	V _{DD} - 1.0	V _{DD} - 0.9	V _{DD} - 0.7	V
	V _{IL}		V _{DD} - 1.9	V _{DD} - 1.7	V _{DD} - 1.6	V
Input Voltage (AC coupled interface)	V _{IN}	Differential Input	0.3	0.8	1.2	VP-P
Input Resistor	R _{IN}	-	-	50	-	Ω
Modulation Peak Current	I _{MMAX}	-	50	-	-	mA
	I _{MMIN}	V _{M1} = V _{SS}	-	-	4	mA
	I _{MDIS}	V _{DISIN} = V _{DD} - 0.2 V	-	-	1	mA
Bias Current	I _{BMAX}	-	50	-	-	mA
	I _{BMIN}	V _{B1} = V _{SS}	-	-	4	mA
	I _{BDIS}	V _{DISIN} = V _{DD} - 0.2 V	-	-	1	mA
Input Voltage (DIS)	V _{DISIH}	Disable operation	V _{DD} - 0.2	-	V _{DD}	mA
	V _{DISIL}	Enable operation	V _{SS}	OPEN	V _{SS} +0.2	mA
Input Voltage (SEL)	V _{SELIH}	Non - Clocked op.	V _{DD} - 0.2	-	V _{DD}	mA
	V _{SELIL}	Clocked operation	V _{SS}	OPEN	V _{SS} + 0.2	mA
Bias Monitor Resistor	R _{BM}		-	5	-	Ω
Rise Time	tr	RL = 25 Ω 20% - 80%	-	80	-	ps
Fall Time	tf	RL = 25 Ω 20% - 80%	-	80	-	ps
Setup Time	ts		-	100	-	ps
Hold Time	th		-	50	-	ps
Maximum Clock Frequency	fmax	V _{SEL} =OPEN or V _{DD} - 0.2 V to V _{DD}	2.5	-	-	GHz
Maximum Data Rate	fopr	V _{SEL} = V _{DD} - 0.2 V to V _{DD}	2.5	-	-	Gbps

*1 Excluding the input current, the modulation current and the bias current.

◆ Block Diagram



◆ Pin Descriptions

Symbol	Description
V _{DDC}	Supply Voltage. V _{DDC} and V _{DDO} are not connected internally.
V _{DDO}	Supply Voltage.
V _{SS}	Supply Voltage.
D _{IN}	Positive data input
D _{INB}	Negative data input
V _{TTD}	Termination data input
CK _{IN}	Positive clock input
CK _{INB}	Negative clock input
V _{TTCK}	Termination for clock input
OUT	Positive modulation output (LD should be connected to this pin.)
OUT _B	Negative modulation output
OUT _{BIAS}	Bias output. (RBM = 5 Ω typ., R _{BMO} =R _{BMOB} = 3 kΩ typ.)
V _{M0} , V _{M1}	Voltage input that sets the LD modulation peak current. V _{M0} and V _{M1} have different control characteristic. If one pin is used, the other must be opened.
V _{B0} , V _{B1}	Voltage input that sets the LD bias current. V _{B0} and V _{B1} have different control characteristic. If one pin is used, the other must be opened.
DIS _{IN}	Voltage input that controls turning on/off modulation current and the bias current
SEL _{IN}	Voltage input that selects clocked or non-clocked operation
BM	Bias current monitor positive output
BM _b	Bias current monitor negative output
V _{REG}	Voltage input that regulate circuit current

◆ **Function Table**

(1) Clocked Operation ($V_{IN} @ SEL_{IN} = OPEN$ or V_{SS} to $V_{SS} + 0.2$ V)

Input		Output	
D_{IN}	CK_{IN}	Current @ OUT	Current @ OUT
H	↑	ON	OFF
L	↑	OFF	ON
Φ	↓	Q_O	Q_{OB}

↓ : Clock transition from high to low

↑ : Clock transition from low to high

Φ : Don't care

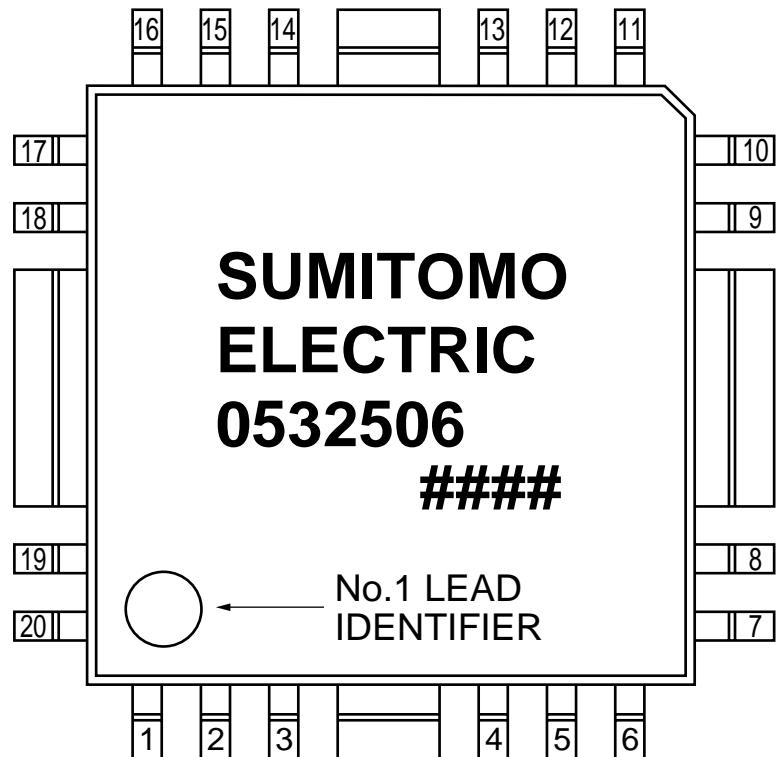
Q_O : Previous current output status @ OUT before clock pulse

Q_{OB} : Previous current output status @ OUTB before clock pulse

(2) Non-clocked Operation ($V_{IN} @ SEL_{IN} = V_{DD} - 0.2$ V to V_{DD})

Input		Output	
D_{IN}	CK_{IN}	Current @ OUT	Current @ OUTB
H	Φ	ON	OFF
L	Φ	OFF	ON

◆ **Pin Assignments (Top View)**

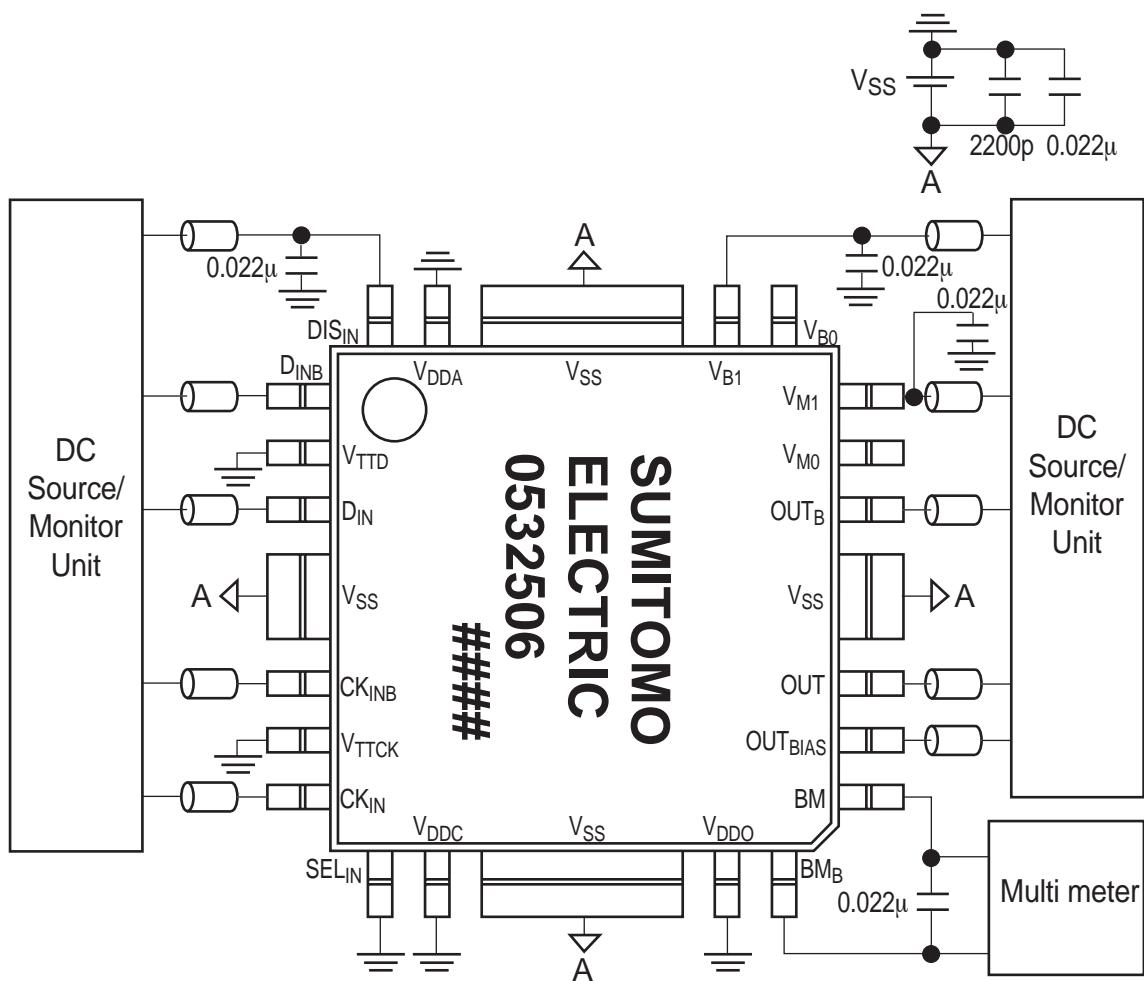


1 :D _{INB}	10 :BM _B	19 :V _{DDA}
2 :V _{TTD}	11 :BM	20 :DIS _{IN}
3 :D _{IN}	12 :OUT _{BIAS}	
4 :CK _{IN}	13 :OUT	
5 :V _{TTCK}	14 :OUT _B	
6 :CK _{INB}	15 :V _{M0}	
7 :SEL _{IN}	16 :V _{M1}	
8 :V _{DDC}	17 :V _{B0}	
9 :V _{DDO}	18 :V _{B1}	

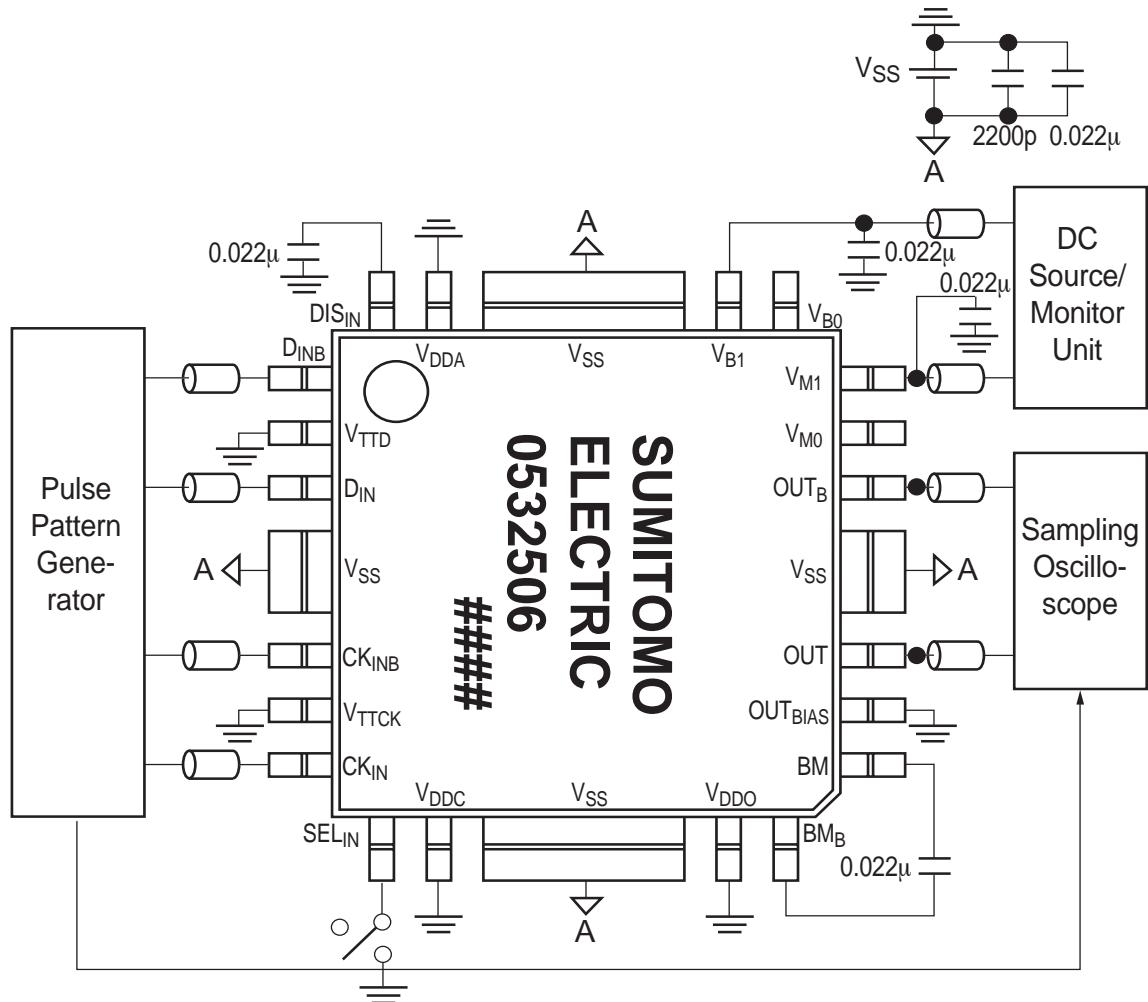
(Note) The pins without numbering should be connected to V_{SS}.
 V_{DDA}, V_{DDC} and V_{DDO} are not connected internally.

◆ Test Circuits

(1) DC Characteristics



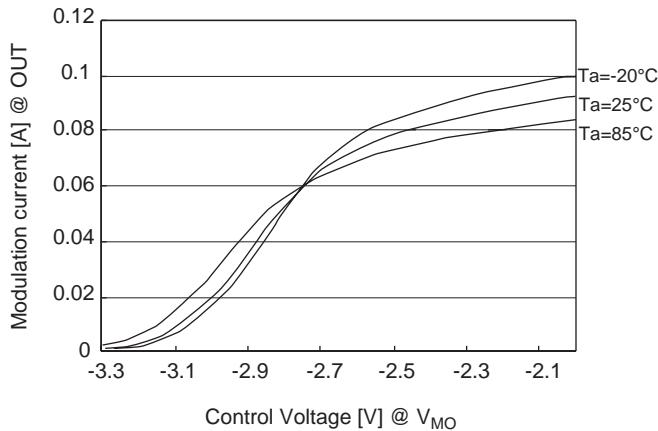
(2) AC Characteristics



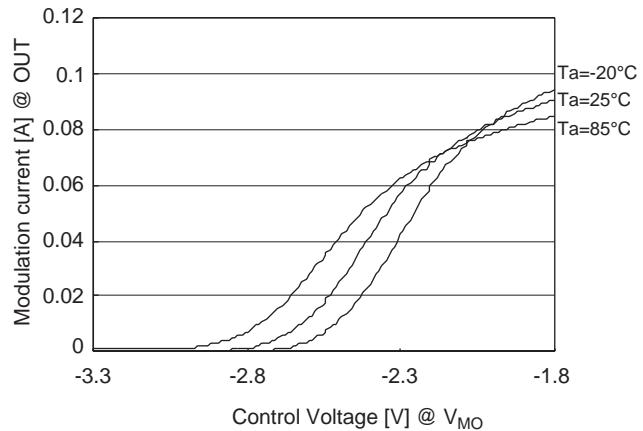
◆ Typical Characteristics

(1) Modulation Current

Modulation Current vs VM0



Modulation Current vs VM1



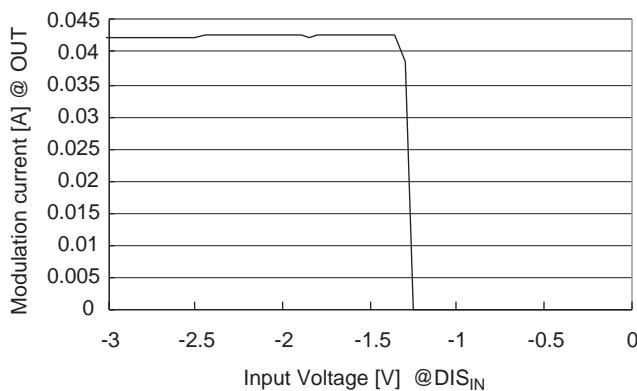
Conditions

V_{OUT} @OUT=GND, V_{DD} =GND, V_{SS} =-3.3V
 V_{IN} @D_{IN}=-1.0V, V_{IN} @D_{INB}=-1.6V
 V_{OUT} @OUTB, OUT_{Bias}=GND
 V_{M1} =Open

Conditions

V_{OUT} @OUT=GND, V_{DD} =GND, V_{SS} =-3.3V
 V_{IN} @D_{IN}=-1.0V, V_{IN} @D_{INB}=-1.6V
 V_{OUT} @OUTB, OUT_{Bias}=GND
 V_{M1} =Open

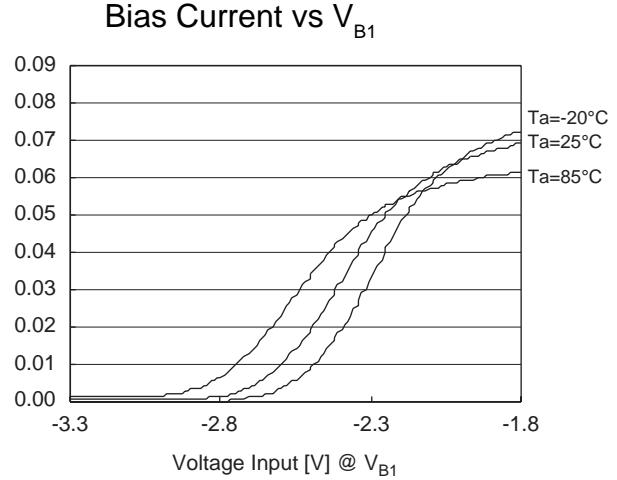
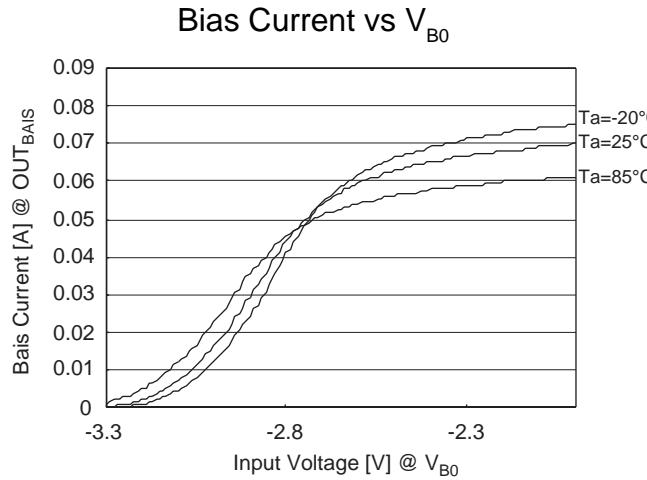
Modulation Current vs DIS_{IN}



Conditions

V_{OUT} @OUT=GND, V_{DD} =GND, V_{SS} =-3.3V
 V_{IN} @D_{IN}=-1.0V, V_{IN} @D_{INB}=-1.6V
 V_{OUT} @OUTB, OUT_{Bias}=GND
 $T_a=25^{\circ}C$

(2) Bias Current

**Conditions**

$V_{OUT}@OUT_{BIAS} = \text{GND}$, $V_{DD} = \text{GND}$, $V_{SS} = -3.3\text{V}$
 $V_{IN}@D_{IN} = -1.0\text{V}$, $V_{IN}@D_{INB} = -1.6\text{V}$
 $V_{OUT}@OUT$, $OUTB = \text{GND}$
 $V_{B1} = \text{Open}$

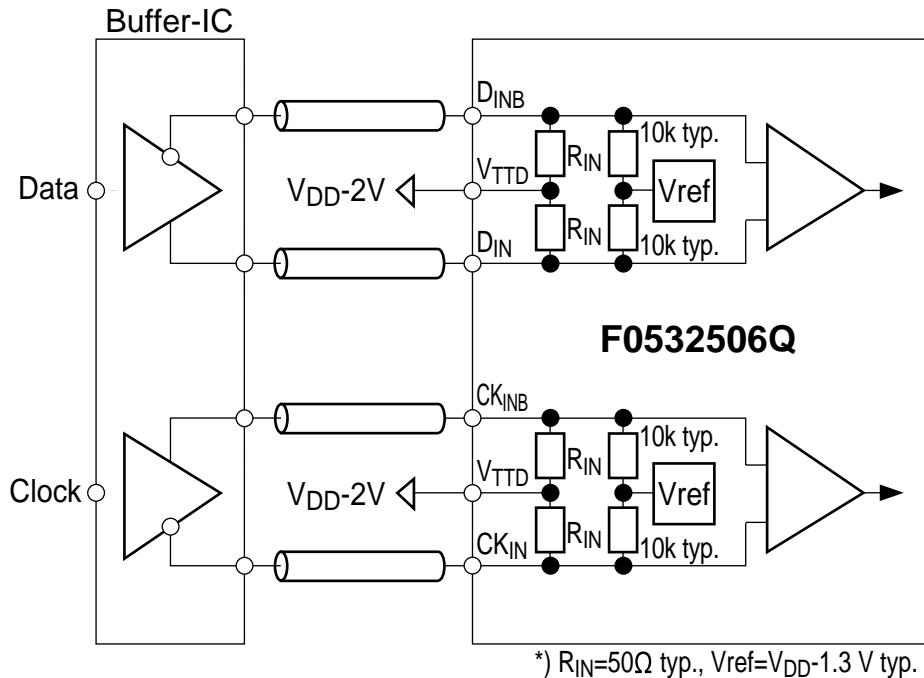
Conditions

$V_{OUT}@OUT_{BIAS} = \text{GND}$, $V_{DD} = \text{GND}$, $V_{SS} = -3.3\text{V}$
 $V_{IN}@D_{IN} = -1.0\text{V}$, $V_{IN}@D_{INB} = -1.6\text{V}$
 $V_{OUT}@OUT$, $OUTB = \text{GND}$
 $V_{B0} = \text{Open}$

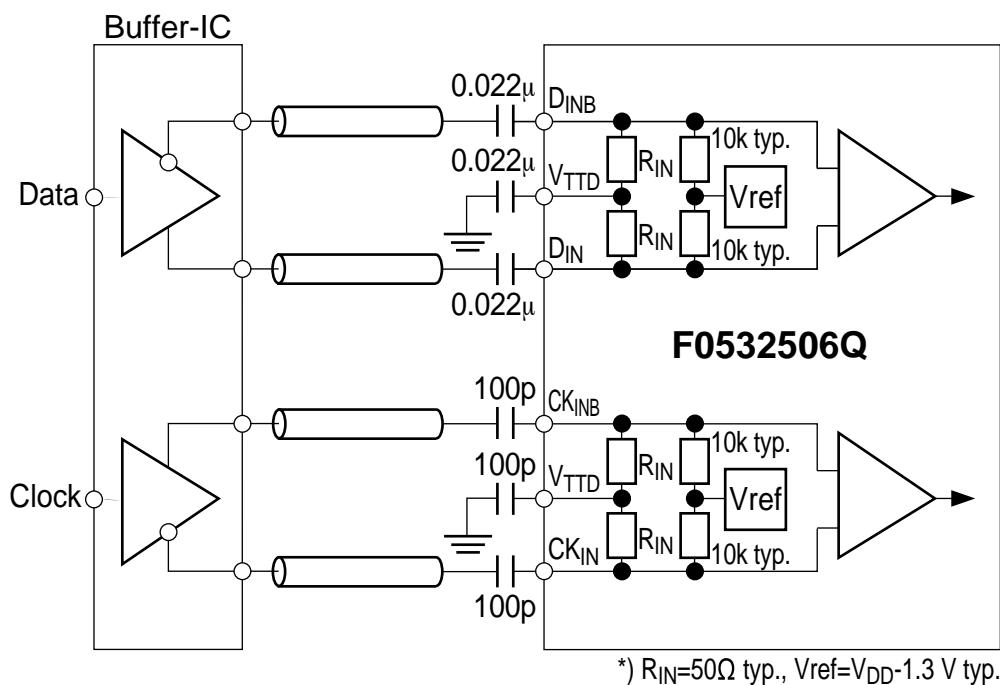
◆ Application Guide

(1) Data and Clock Input Interface

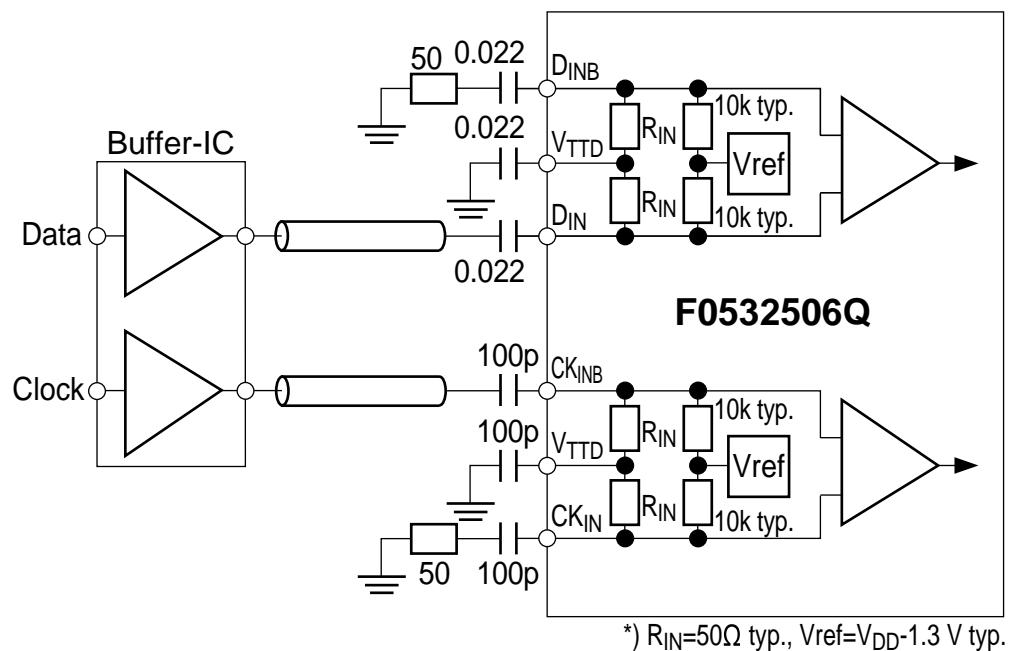
(a) Differential ECL (or PECL) Interface



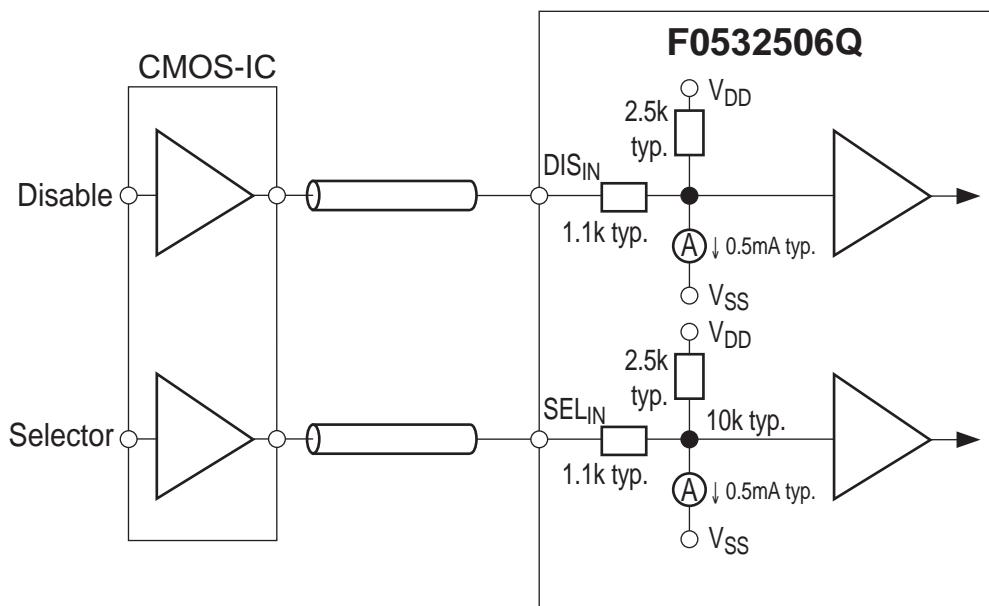
(b) Differential AC Coupled Interface



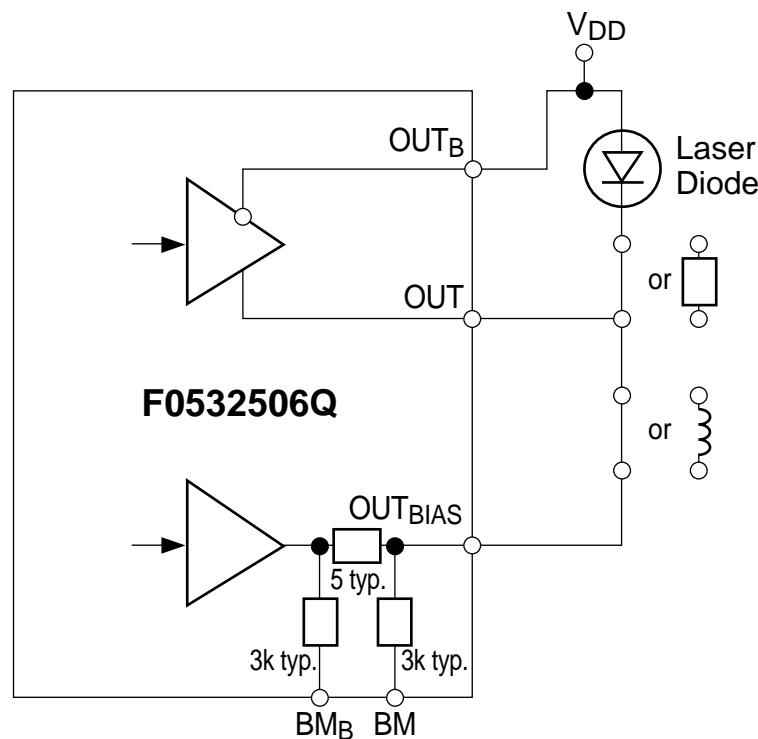
(c) Single-Ended AC Coupled Interface



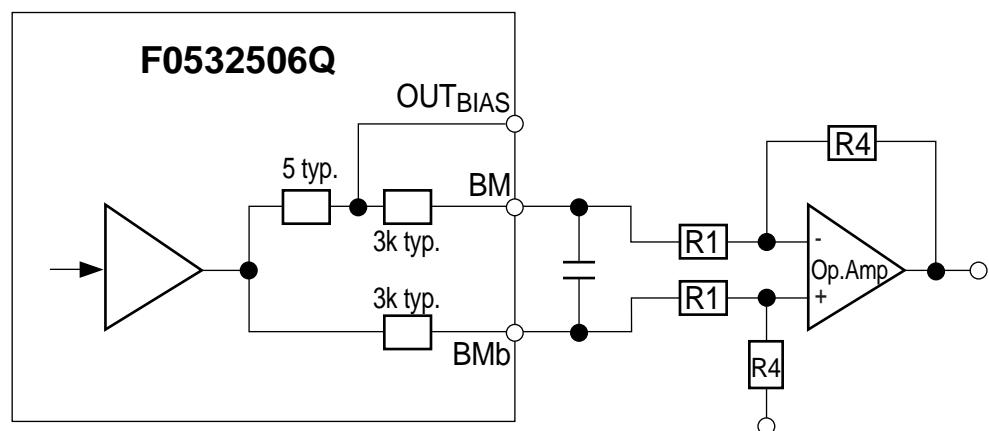
(2) Disable Input and Selector Input Interface



(3) Current Output Interface

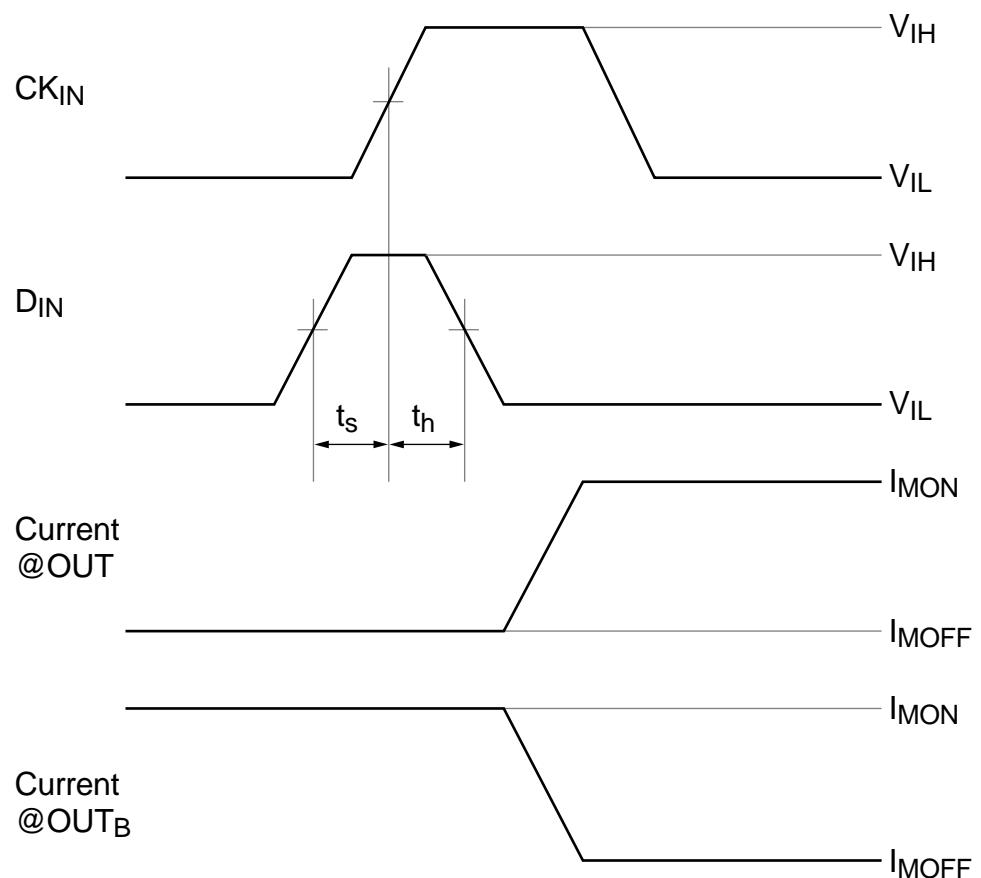


(4) Bias Current Monitor



*) Value of R1 to R4 should be enough larger than 25Ω .
Recommended value is 100K to 200 K Ω .

(5) Timing Chart



◆ Package Drawings